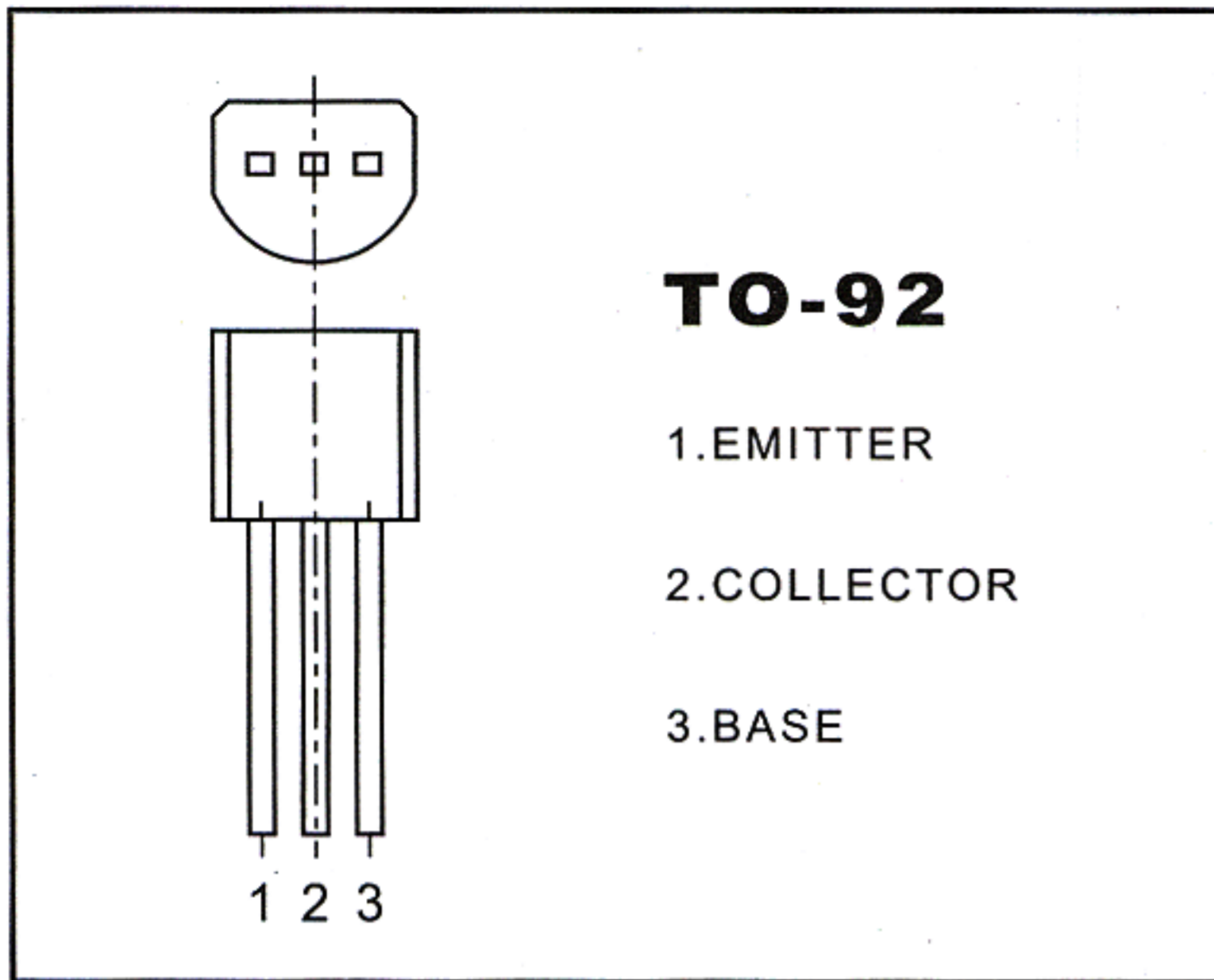


TO-92 Plastic-Encapsulate Transistors

BF420 BF422 TRANSISTOR(NPN)



FEATURES

Power dissipation

P_{CM} : 0.83W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : 0.1 A

Collector-base voltage

$V_{(BR)CBO}$: BF420 : 300V

BF422 : 250V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

ELECTRICAL CHARACTERISTICS

($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	V_{CBO}	$I_C = 100 \mu A, I_E = 0$	300		V
			250		
Collector-emitter breakdown voltage	V_{CEO}	$I_C = 1 mA, I_B = 0$	300		V
			250		
Emitter-base breakdown voltage	V_{EBO}	$I_E = 100 \mu A, I_C = 0$	5		V
Collector cut-off current	I_{CBO}	$V_{CB} = 200 V, I_E = 0$		0.01	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5 V, I_C = 0$		0.05	μA
DC current gain	h_{FE}	$V_{CE} = 20 V, I_C = 25 mA$	50		
Collector-emitter saturation voltage	V_{CEsat}	$I_C = 30 mA, I_B = 5 mA$		0.6	V
Transition frequency	f_T	$V_{CE} = 10 V, I_C = 10 mA$ $f = 100 MHz$	60		MHz